

1. General description

Dual Silicon Carbide Schottky diode in a TO247 plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- New 6th Generation Technology
- Low Forward Voltage Drop
- Low Reverse Leakage Current
- High Forward Surge Capability IFSM
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

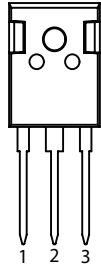
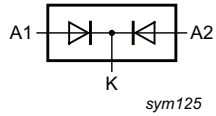
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{RRM}	repetitive peak reverse voltage			650			V
$I_{O(AV)}$	limiting average forward current	$\delta = 0.5$; square-wave pulse; $T_{mb} \leq 139$ °C; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3		30			A
T_j	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V_F	forward voltage	$I_F = 15$ A; $T_j = 25$ °C; per diode; Fig. 5		-	1.26	1.40	V
		$I_F = 15$ A; $T_j = 150$ °C; per diode; Fig. 5		-	1.35	1.55	V
Dynamic characteristics							
Q_r	recovered charge	$I_F = 15$ A; $di_F/dt = 500$ A/ μ s; $V_R = 400$ V; $T_j = 25$ °C; per diode; Fig. 7		-	36	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN6D30650CW	TO247	WN6D30650CW6Q	Tube	30	TO247N	20-July-2016

7. Marking

Table 4. Marking codes

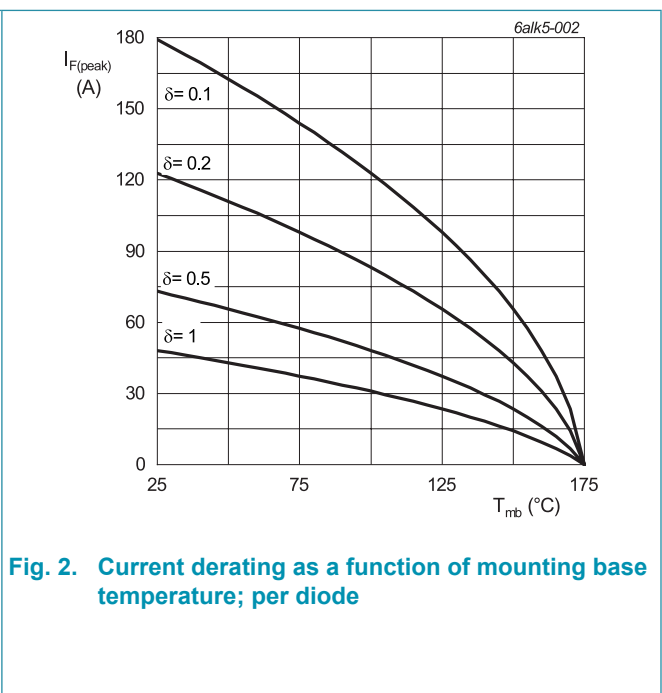
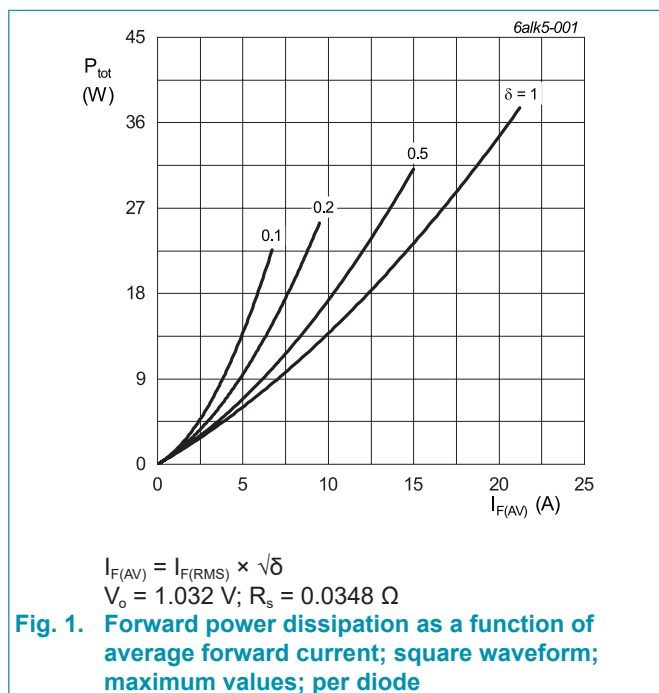
Type number	Marking codes
WN6D30650CW	WN6D 30650CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			650	V
V_{RWM}	crest working reverse voltage			650	V
V_R	reverse voltage	DC		650	V
$I_{O(AV)}$	limiting average forward current	$\delta = 0.5$; square-wave pulse; $T_{mb} \leq 139\text{ }^\circ\text{C}$; both diodes conducting; Fig. 1 ; Fig. 2 ; Fig. 3		30	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 141\text{ }^\circ\text{C}$; square-wave pulse; per diode		30	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; sine-wave pulse; per diode		120	A
		$t_p = 10\text{ }\mu\text{s}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; square-wave pulse; per diode		900	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; $t_p = 10\text{ ms}$		72	A^2s
T_{stg}	storage temperature			-55 to 175	$^\circ\text{C}$
T_j	junction temperature			-55 to 175	$^\circ\text{C}$



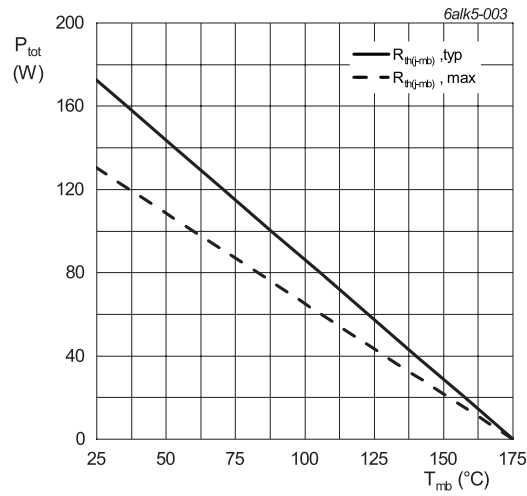


Fig. 3. Total power dissipation as a function of mounting base temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	per diode; Fig. 4		-	0.87	1.15	K/W
		both diodes conducting		-	-	0.55	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

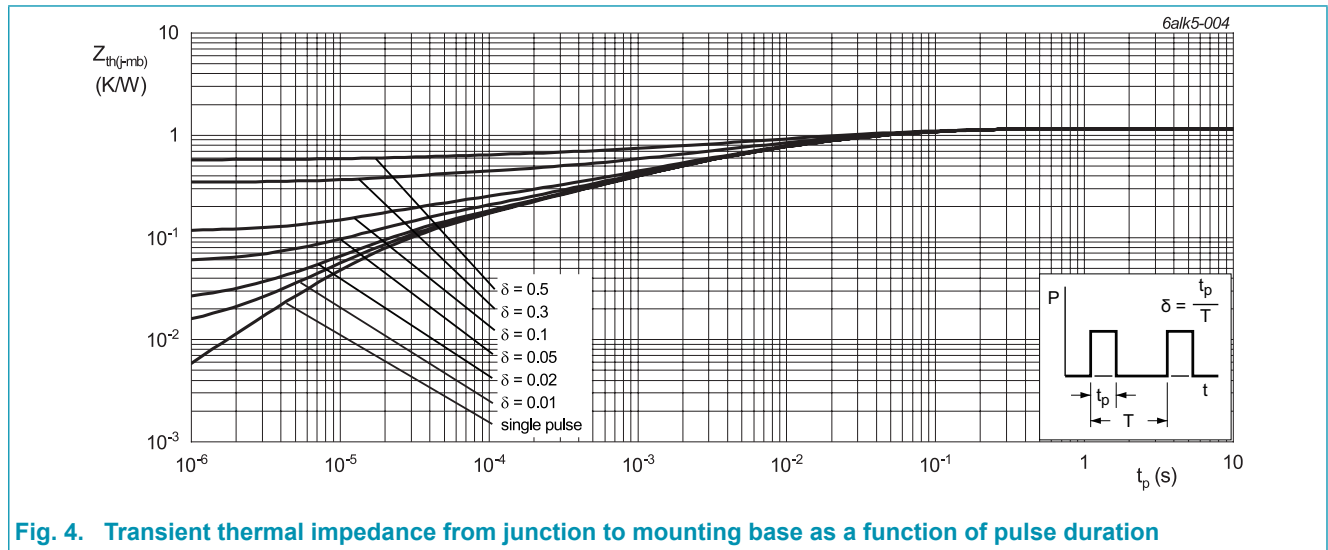
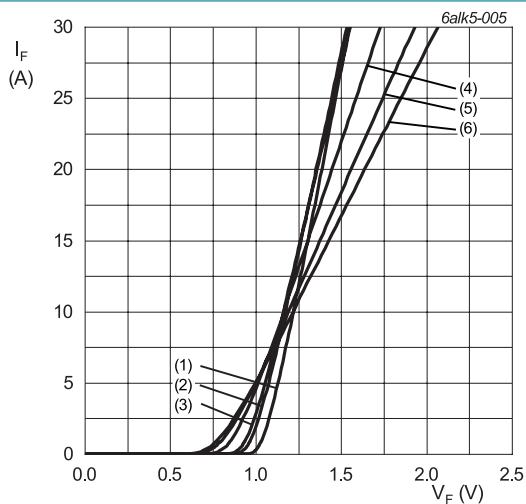


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
V_F	forward voltage	$I_F = 15\text{ A}; T_j = 25\text{ }^\circ\text{C};$ per diode; Fig. 5		-	1.26	1.40	V
		$I_F = 15\text{ A}; T_j = 150\text{ }^\circ\text{C};$ per diode; Fig. 5		-	1.35	1.55	V
		$I_F = 15\text{ A}; T_j = 175\text{ }^\circ\text{C};$ per diode; Fig. 5		-	1.40	1.60	V
I_R	reverse current	$V_R = 650\text{ V}; T_j = 25\text{ }^\circ\text{C};$ per diode; Fig. 6		-	1	80	μA
		$V_R = 650\text{ V}; T_j = 175\text{ }^\circ\text{C};$ per diode; Fig. 6		-	25	320	μA
Dynamic characteristics							
Q_r	recovered charge	$I_F = 15\text{ A}; V_R = 400\text{ V}; dI_F/dt = 500\text{ A}/\mu\text{s};$ $T_j = 25\text{ }^\circ\text{C};$ per diode; Fig. 7		-	36	-	nC
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 1\text{ V}; T_j = 25\text{ }^\circ\text{C};$ per diode		-	780	-	pF
		$f = 1\text{ MHz}; V_R = 300\text{ V}; T_j = 25\text{ }^\circ\text{C};$ per diode		-	86	-	pF
		$f = 1\text{ MHz}; V_R = 600\text{ V}; T_j = 25\text{ }^\circ\text{C};$ per diode		-	79	-	pF
E_{as}	non-repetitive avalanche energy	$I_R = 7\text{ A}; L = 5\text{ mH}; T_{j(\text{init})} = 25\text{ }^\circ\text{C};$ per diode		120	-	-	mJ



$V_o = 1.032\text{ V}; R_s = 0.0348\ \Omega$
 (1) $T_j = -55\text{ }^\circ\text{C};$ typical values
 (2) $T_j = 0\text{ }^\circ\text{C};$ typical values
 (3) $T_j = 25\text{ }^\circ\text{C};$ typical values
 (4) $T_j = 100\text{ }^\circ\text{C};$ typical values
 (5) $T_j = 150\text{ }^\circ\text{C};$ typical values
 (6) $T_j = 175\text{ }^\circ\text{C};$ typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

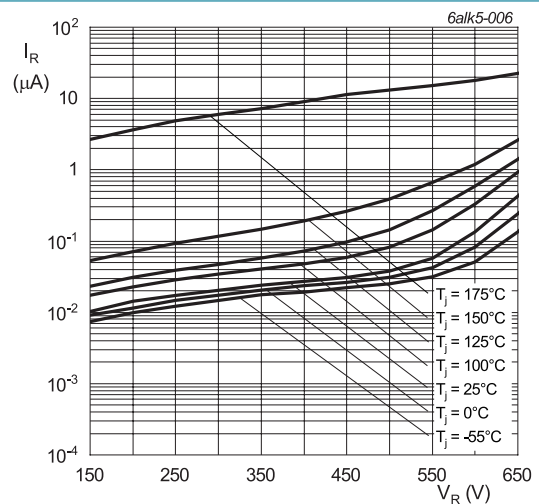


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

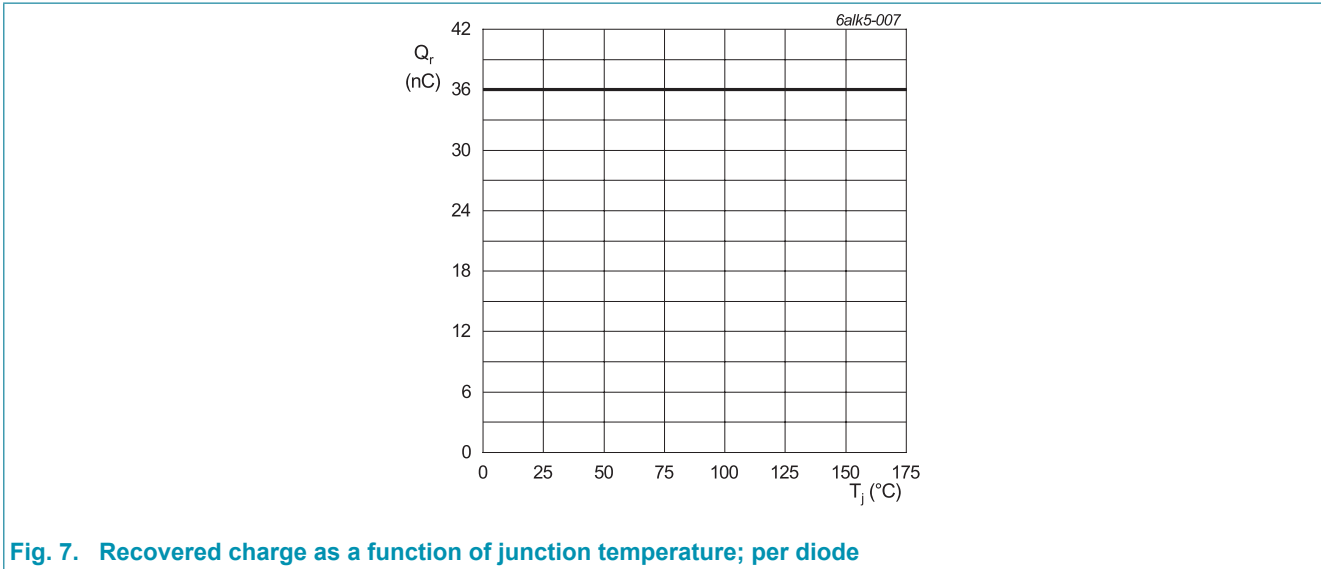
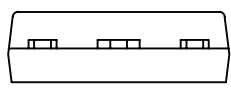
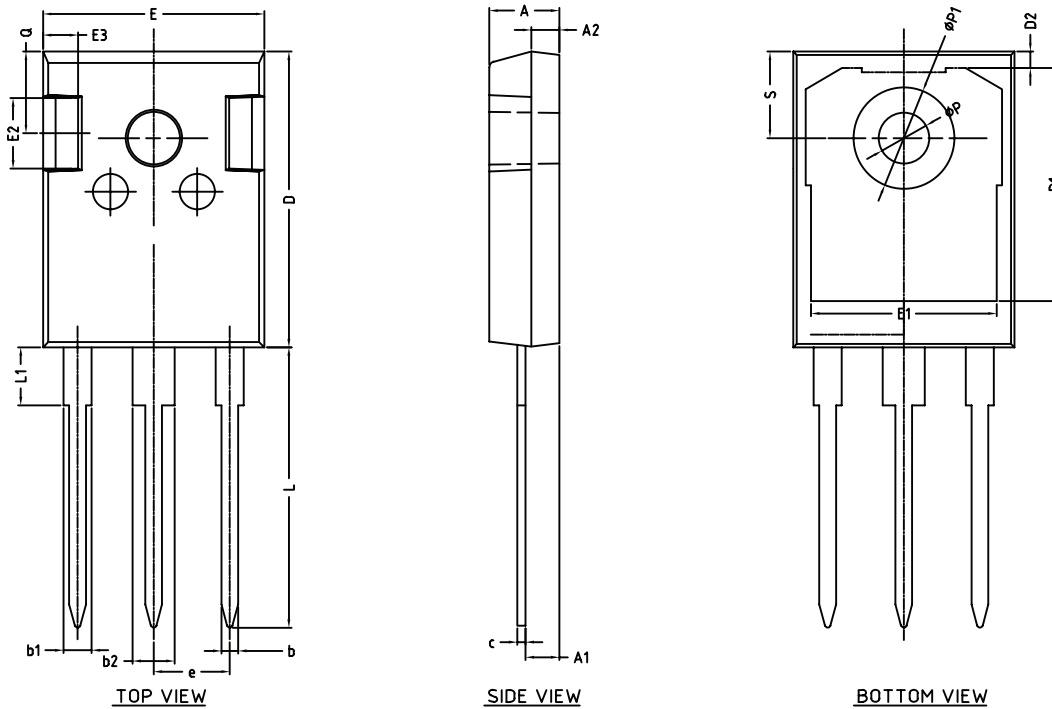


Fig. 7. Recovered charge as a function of junction temperature; per diode

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429N



SIDE VIEW

UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	MAX	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	20.10	4.75	3.70	7.40	6.00	6.25
	MIN	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40	5.45	19.80	-	3.50	-	5.60

OUTLINE VERSION	REFERENCES			PROJECTION	ISSUE DATE
	IEC	JEDEC	EIA J		
SOT429N		TO-247			

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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